Dual P-Channel Enhancement Mode Power MOSFET

Description

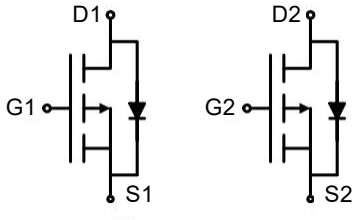
The G200P04S2 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

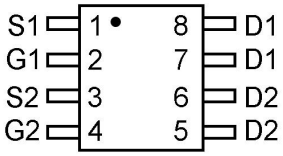
- V_{DS} -40V
- I_D (at V_{GS} = -10V) -9A
- $R_{DS(ON)}$ (at V_{GS} = -10V) < 20mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V) < 25mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



pin assignment

SOP-8

Ordering Information

Device	Package	Marking	Packaging
G200P04S2	SOP-8 Dual	G200P04S2	4000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Continuous Drain Current	I_D	-9	A
Pulsed Drain Current (note1)	I_{DM}	-36	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	2.1	W
Single pulse avalanche energy （note2）	E_{AS}	81	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	59	ºC/W

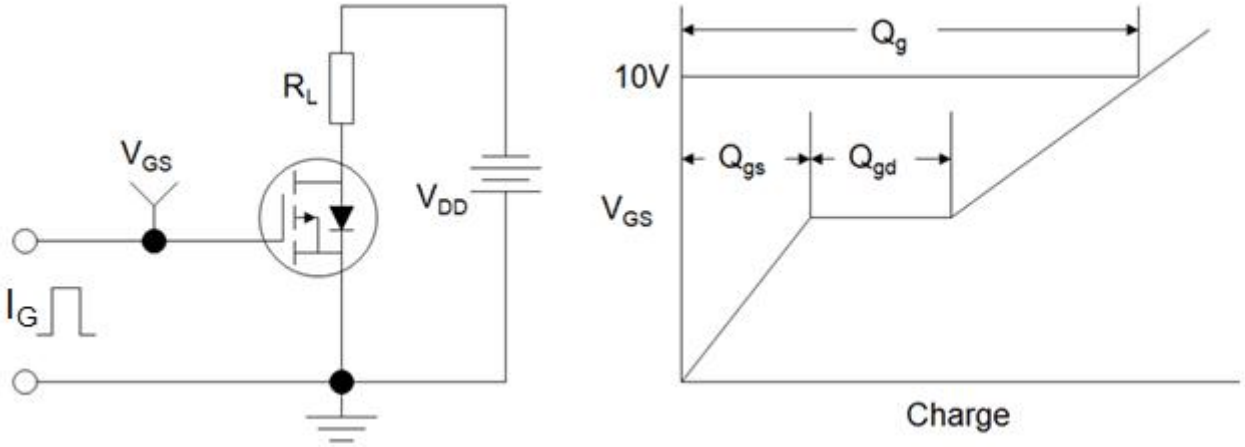
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -40V, V_{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -7A	--	16	20	mΩ
		V_{GS} = -4.5V, I_D = -7A	--	20	25	
Forward Transconductance	g_{FS}	V_{DS} = -5V,I_D = -7A	--	16	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -20V, f = 1.0MHz	--	2365	--	pF
Output Capacitance	C_{oss}		--	221	--	
Reverse Transfer Capacitance	C_{rss}		--	208	--	
Total Gate Charge	Q_g	V_{DD} = -20V, I_D = -7A, V_{GS} = -10V	--	42	--	nC
Gate-Source Charge	Q_{gs}		--	7	--	
Gate-Drain Charge	Q_{gd}		--	8.6	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -20V, I_D = -7A, R_G = 3Ω	--	20	--	ns
Turn-on Rise Time	t_r		--	9.4	--	
Turn-off Delay Time	$t_{d(off)}$		--	55	--	
Turn-off Fall Time	t_f		--	30	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-9	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -7A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	I_F = -7A, V_{GS} = 0V di/dt=-100A/us	--	47	--	nC
Reverse Recovery Time	T_{rr}		--	38	--	ns

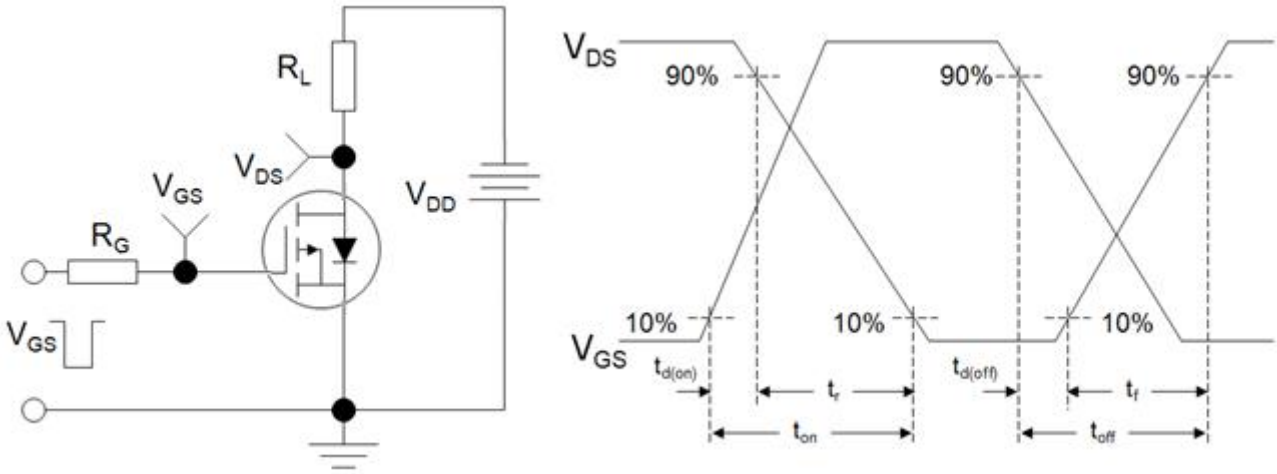
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=-40V,VGS=-10V,L=0.5mH,Rg=25Ω
3. Identical low side and high side switch with identical R_G

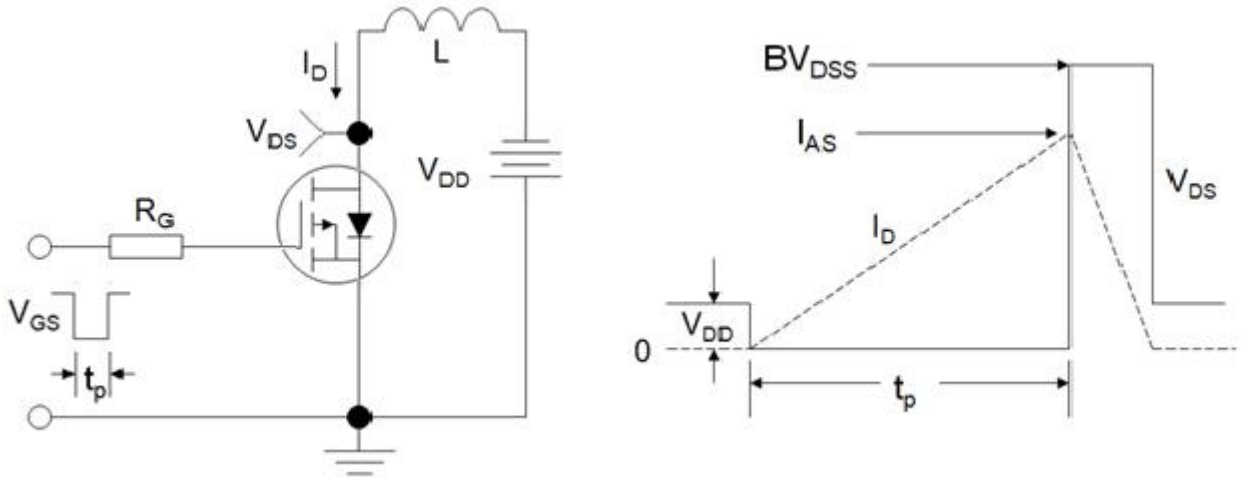
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

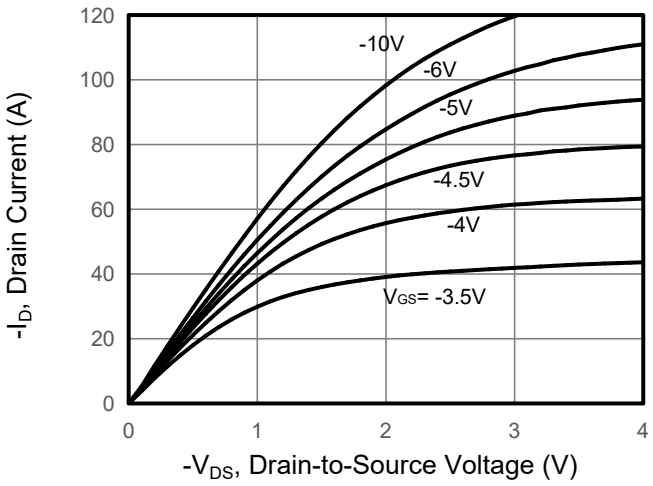


Figure 2. Transfer Characteristics

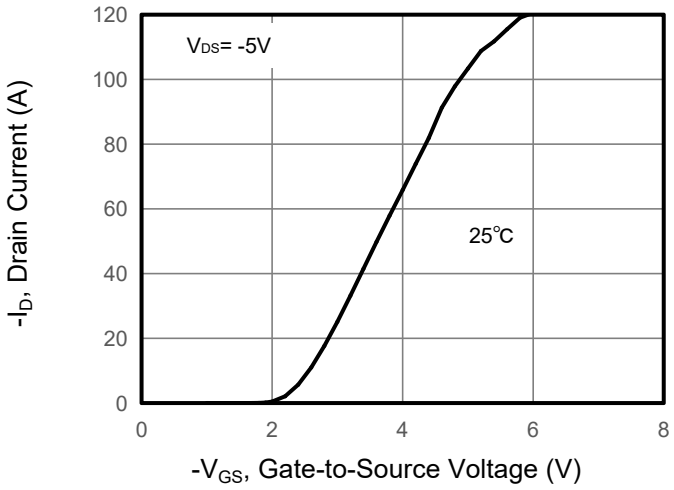


Figure 3.Drain Source On Resistance

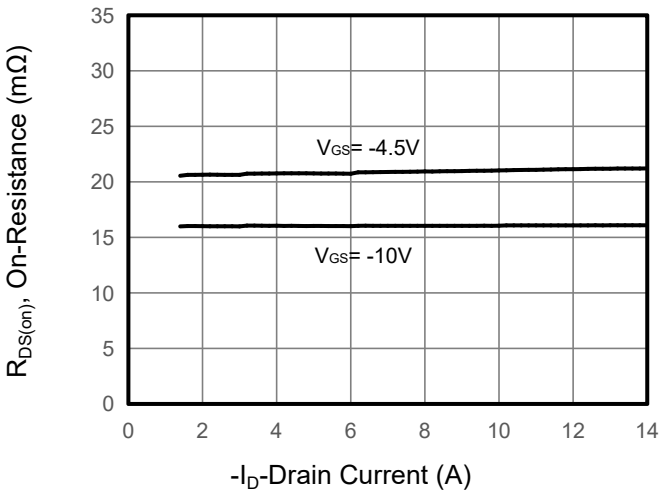


Figure 4. Gate Charge

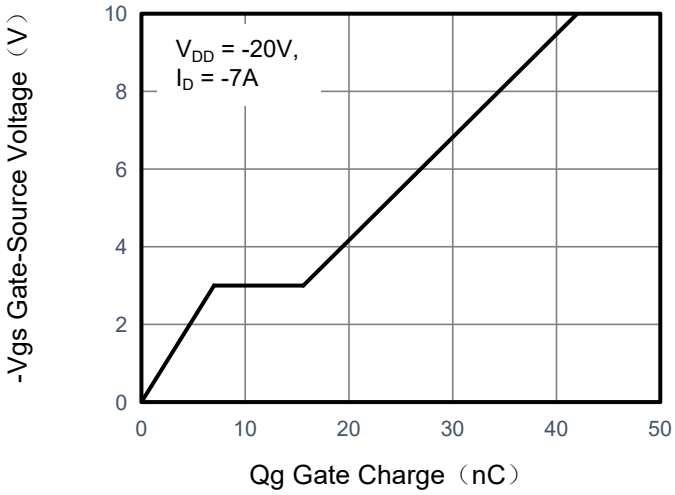


Figure 5. Capacitance

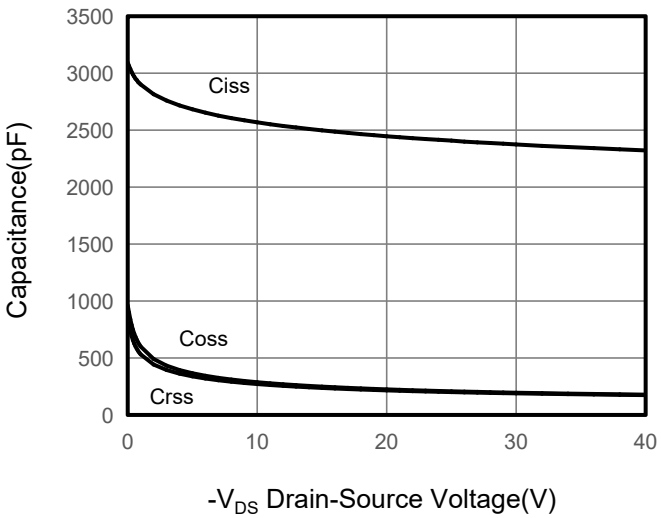
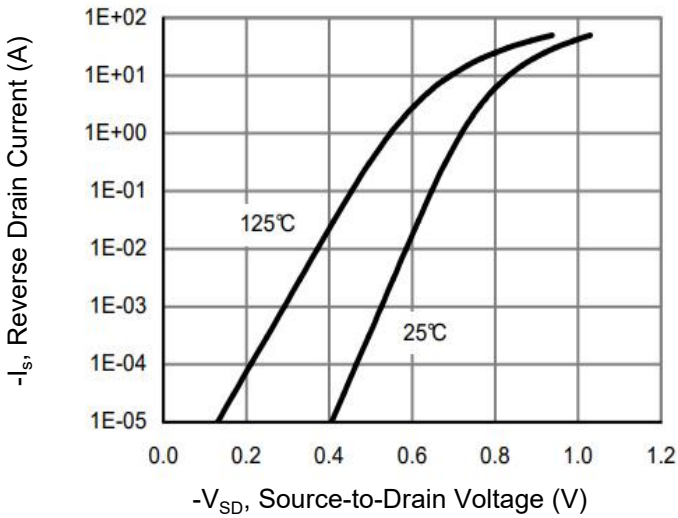


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

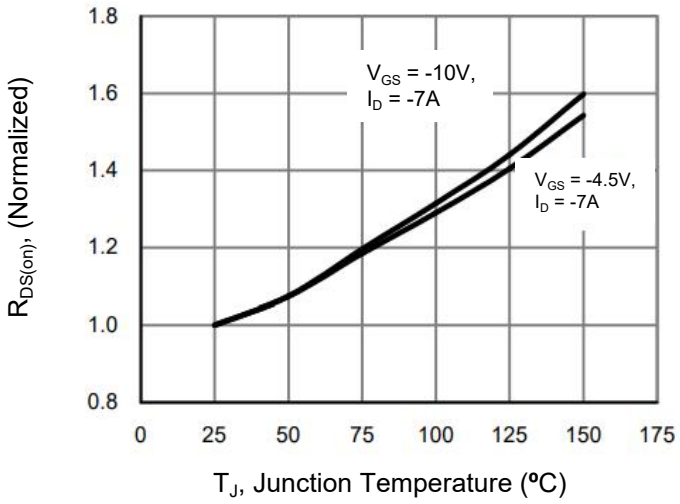


Figure 10. Safe Operation Area

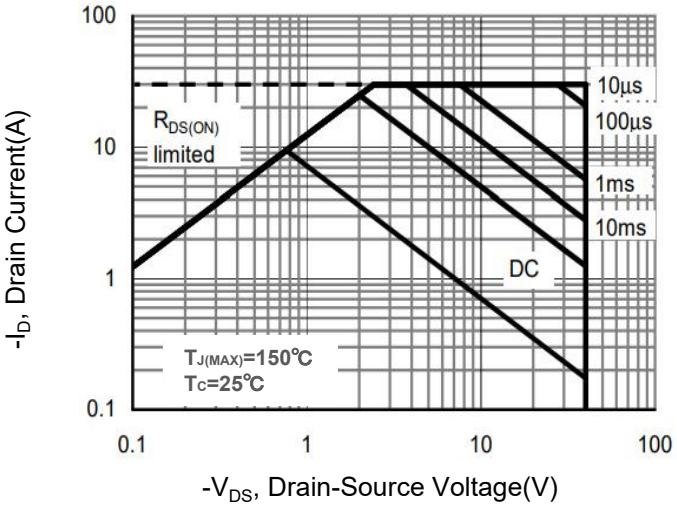
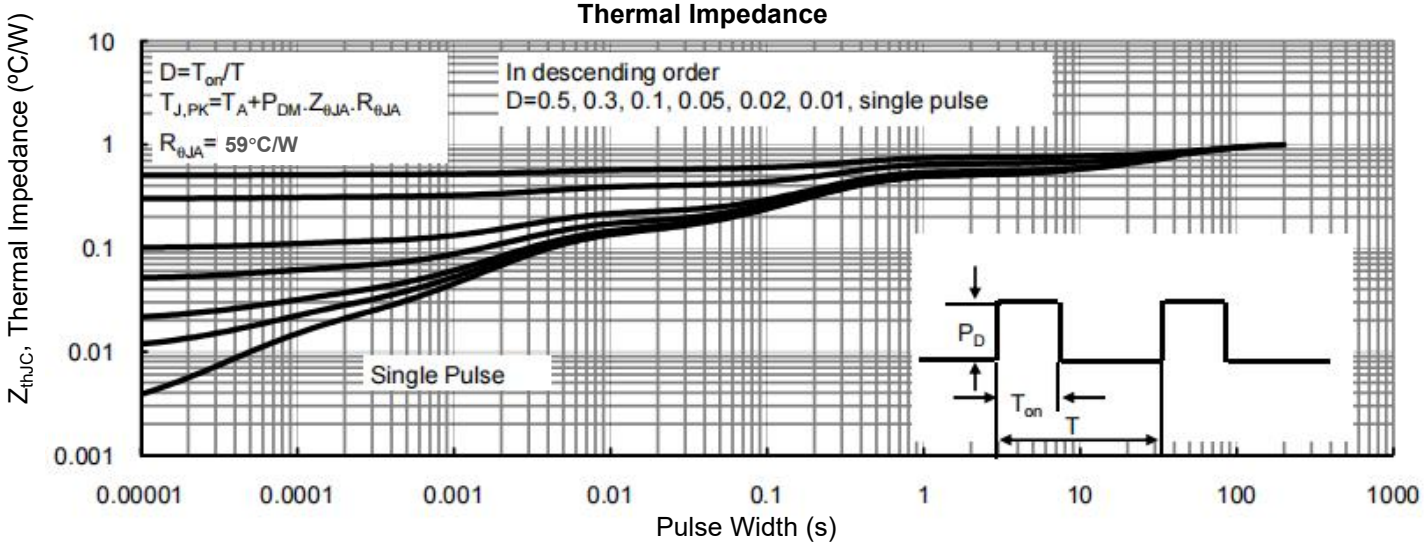
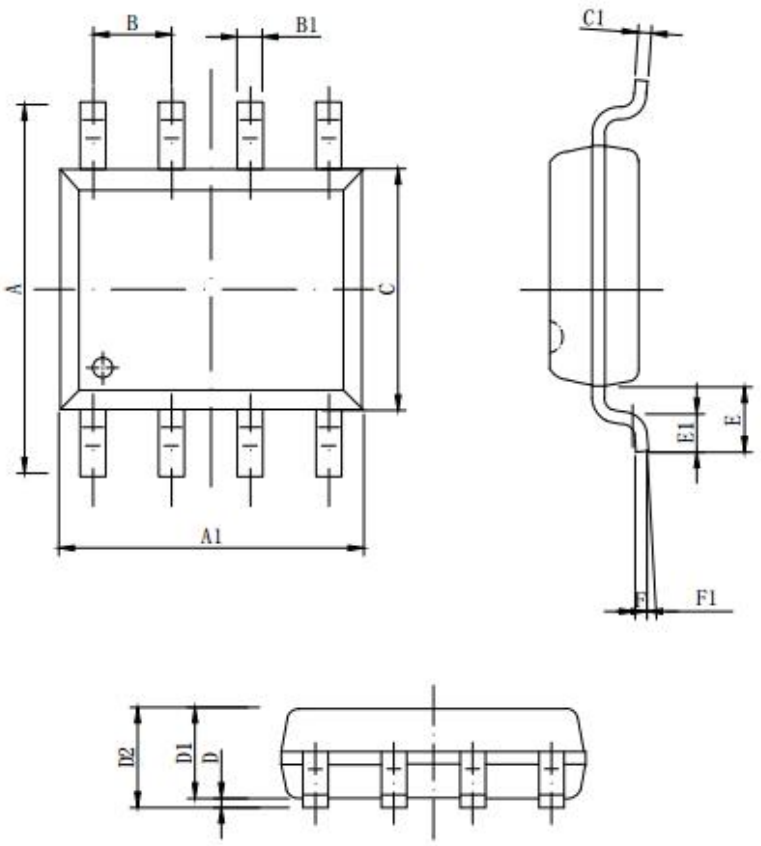


Figure 9. Normalized Maximum Transient Thermal Impedance



SOP-8 Dual Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B		1.270BSC	
B1	0.35^8x	0.40^8x	0.45^8x
C	3.780	3.880	3.980
C1	--	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
D2	1.500	1.600	1.700
E		1.060REF	
E1	0.400	0.700	0.100
F		0.250BSC	
F1	2°	4°	6°